

## METHODS FOR FORMING ELECTRONIC DEVICES INCLUDING CAPACITOR STRUCTURES

### Abstract of the Disclosure

5           Methods for forming an electronic device can include forming a  
capacitor structure on a portion of a substrate with the capacitor structure  
including a first electrode on the substrate, a capacitor dielectric on the first  
electrode, a second electrode on the dielectric, and a hard mask on the second  
electrode. More particularly, the capacitor dielectric can be between the first  
10   and second electrodes, the first electrode and the capacitor dielectric can be  
between the second electrode and the substrate, and the first and second  
electrodes and the capacitor dielectric can be between the hard mask and the  
substrate. An interlayer dielectric layer can be formed on the hard mask and on  
portions of the substrate surrounding the capacitor structure, and portions of the  
15   interlayer dielectric layer can be removed to expose the hard mask while  
maintaining portions of the interlayer dielectric layer on portions of the  
substrate surrounding the capacitor structure. The hard mask can then be  
removed thereby exposing portions of the second electrode while maintaining  
the portions of the interlayer dielectric layer on portions of the substrate  
20   surrounding the capacitor.